

## Digital Transistors (BRT) R1 = 4.7 k $\Omega$ , R2 = 47 k $\Omega$

PNP Transistors with Monolithic Bias Resistor Network

## MUN2133, MMUN2133L, MUN5133, DTA143ZE, DTA143ZM3, NSBA143ZF3

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

#### **Features**

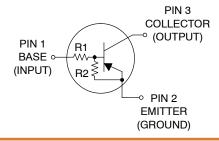
- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

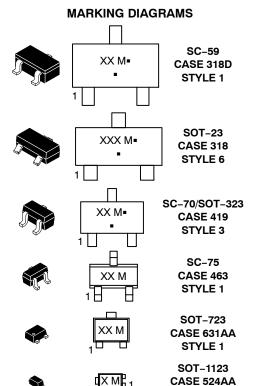
#### MAXIMUM RATINGS (T<sub>A</sub> = 25°C)

Rating	Symbol	Max	Unit
Collector-Base Voltage	$V_{CBO}$	50	Vdc
Collector-Emitter Voltage	$V_{CEO}$	50	Vdc
Collector Current - Continuous	I <sub>C</sub>	100	mAdc
Input Forward Voltage	$V_{IN(fwd)}$	30	Vdc
Input Reverse Voltage	V <sub>IN(rev)</sub>	5	Vdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### **PIN CONNECTIONS**





XXX = Specific Device Code M = Date Code\* ■ Pb-Free Package

STYLE 1

(Note: Microdot may be in either location)

#### **ORDERING INFORMATION**

See detailed ordering, marking, and shipping information on page 2 of this data sheet.

NOTE: Some of the devices on this data sheet have been **DISCONTINUED**. Please refer to the table on page 2.

<sup>\*</sup>Date Code orientation may vary depending upon manufacturing location.

**Table 1. ORDERING INFORMATION** 

Device	Part Marking	Package	Shipping <sup>†</sup>
MUN2133T1G	6K	SC-59 (Pb-Free)	3000 / Tape & Reel
MMUN2133LT1G, NSVMMUN2133LT1G	A6K	SOT-23 (Pb-Free)	3000 / Tape & Reel
MUN5133T1G, SMUN5133T1G	6K	SC-70/SOT-323 (Pb-Free)	3000 / Tape & Reel
DTA143ZET1G, NSVDTA143ZET1G	6K	SC-75 (Pb-Free)	3000 / Tape & Reel
DTA143ZM3T5G	6K	SOT-723 (Pb-Free)	8000 / Tape & Reel

#### **DISCONTINUED** (Note 1)

NSBA143ZF3T5G	E(90°)*	SOT-1123 (Pb-Free)	8000 / Tape & Reel
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<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>1.</sup> **DISCONTINUED:** This device is not recommended for new design. Please contact your **onsemi** representative for information. The most current information on this device may be available on <a href="https://www.onsemi.com">www.onsemi.com</a>.

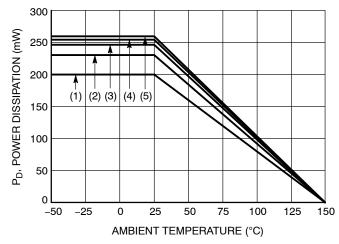


Figure 1. Derating Curve

- (1) SC-75 and SC-70/SOT-323; Minimum Pad
- (2) SC-59; Minimum Pad
- (3) SOT-23; Minimum Pad
- (4) SOT-1123; 100 mm<sup>2</sup>, 1 oz. copper trace
- (5) SOT-723; Minimum Pad

 $<sup>*(</sup>XX^{\circ})$  = Degree rotation in the clockwise direction.

#### **Table 2. THERMAL CHARACTERISTICS**

Characteristic	Symbol	Max	Unit
THERMAL CHARACTERISTICS (SC-59) (MUN2133)			•
Total Device Dissipation  T <sub>A</sub> = 25°C (Note 2) (Note 3) Derate above 25°C (Note 2) (Note 3)	P <sub>D</sub>	230 338 1.8 2.7	mW mW/°C
Thermal Resistance, (Note 2) Junction to Ambient (Note 3)	$R_{ hetaJA}$	540 370	°C/W
Thermal Resistance, (Note 2) Junction to Lead (Note 3)	$R_{ heta JL}$	264 287	°C/W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
THERMAL CHARACTERISTICS (SOT-23) (MMUN2133L)	•	•	•
Total Device Dissipation  T <sub>A</sub> = 25°C (Note 2)  (Note 3)  Derate above 25°C (Note 2)  (Note 3)	P <sub>D</sub>	246 400 2.0 3.2	mW mW/°C
Thermal Resistance, (Note 2) Junction to Ambient (Note 3)	$R_{ heta JA}$	508 311	°C/W
Thermal Resistance, (Note 2) Junction to Lead (Note 3)	$R_{ heta JL}$	174 208	°C/W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
Thermal Characteristics (SC-70/SOT-323) (MUN5133)	•	•	•
Total Device Dissipation $T_A = 25^{\circ}C \text{ (Note 2)} $ (Note 3) $Derate above 25^{\circ}C \text{ (Note 2)} $ (Note 3)	P <sub>D</sub>	202 310 1.6 2.5	mW mW/°C
Thermal Resistance, (Note 2) Junction to Ambient (Note 3)	$R_{ heta JA}$	618 403	°C/W
Thermal Resistance, (Note 2) Junction to Lead (Note 3)	$R_{ heta JL}$	280 332	°C/W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
Thermal Characteristics (SC-75) (DTA143ZE)			
Total Device Dissipation $T_{A} = 25^{\circ}\text{C (Note 2)} $ (Note 3) $Derate above 25^{\circ}\text{C (Note 2)} $ (Note 3)	P <sub>D</sub>	200 300 1.6 2.4	mW mW/°C
Thermal Resistance, (Note 2) Junction to Ambient (Note 3)	$R_{ heta JA}$	600 400	°C/W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
Thermal Characteristics (SOT-723) (DTA143ZM3)	·		
Total Device Dissipation $T_{A} = 25^{\circ}C \text{(Note 2)} $ (Note 3) $Derate above 25^{\circ}C \text{ (Note 2)} $ (Note 3)	P <sub>D</sub>	260 600 2.0 4.8	mW mW/°C
Thermal Resistance, (Note 2) Junction to Ambient (Note 3)	$R_{\thetaJA}$	480 205	°C/W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

**Table 2. THERMAL CHARACTERISTICS** 

Characteristic		Symbol	Max	Unit
Thermal Characteristics (SOT-1123) (NSBA143ZF3)				
Total Device Dissipation $T_A = 25^{\circ}C \text{ (Note 4)}$ (Note 5) $Derate \text{ above } 25^{\circ}C \text{ (Note 4)}$ (Note 5)		P <sub>D</sub>	254 297 2.0 2.4	mW mW/°C
Thermal Resistance, (Note 4) Junction to Ambient (Note 5)		$R_{ hetaJA}$	493 421	°C/W
Thermal Resistance, Junction to Lead	(Note 4)	$R_{ heta JL}$	193	°C/W
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

<sup>2.</sup> FR-4 @ Minimum Pad.

Table 3. ELECTRICAL CHARACTERISTICS ( $T_A = 25^{\circ}C$ , unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS		ı		L.	<b>!</b>
Collector-Base Cutoff Current (V <sub>CB</sub> = 50 V, I <sub>E</sub> = 0)	Ісво	-	-	100	nAdc
Collector–Emitter Cutoff Current (V <sub>CE</sub> = 50 V, I <sub>B</sub> = 0)	I <sub>CEO</sub>	-	-	500	nAdc
Emitter–Base Cutoff Current $(V_{EB} = 6.0 \text{ V}, I_C = 0)$	I <sub>EBO</sub>	-	-	0.18	mAdc
Collector–Base Breakdown Voltage ( $I_C = 10 \mu A, I_E = 0$ )	V <sub>(BR)</sub> CBO	50	-	-	Vdc
Collector–Emitter Breakdown Voltage (Note 6) (I <sub>C</sub> = 2.0 mA, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	50	-	-	Vdc
ON CHARACTERISTICS		•			•
DC Current Gain (Note 5) (I <sub>C</sub> = 5.0 mA, V <sub>CE</sub> = 10 V)	h <sub>FE</sub>	80	140	-	
Collector – Emitter Saturation Voltage (Note 6) (I <sub>C</sub> = 10 mA, I <sub>B</sub> = 0.3 mA)	VCE(sat)	-	-	0.25	Vdc
Input Voltage (off) $(V_{CE} = 5.0 \text{ V}, I_{C} = 100  \mu\text{A})$	V <sub>i(off)</sub>	-	0.7	0.5	Vdc
Input Voltage (on) ( $V_{CE} = 0.3 \text{ V}, I_{C} = 5.0 \text{ mA}$ )	V <sub>i(on)</sub>	1.3	0.9	-	Vdc
Output Voltage (on) (V <sub>CC</sub> = 5.0 V, V <sub>B</sub> = 2.5 V, R <sub>L</sub> = 1.0 k $\Omega$ )	V <sub>OL</sub>	-	-	0.2	Vdc
Output Voltage (off) (V <sub>CC</sub> = 5.0 V, V <sub>B</sub> = 0.5 V, R <sub>L</sub> = 1.0 k $\Omega$ )	V <sub>OH</sub>	4.9	-	-	Vdc
Input Resistor	R1	3.3	4.7	6.1	kΩ
Resistor Ratio	R <sub>1</sub> /R <sub>2</sub>	0.08	0.1	0.14	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

FR-4 @ 1.0 x 1.0 Inch Pad.
 FR -4 @ 100 mm<sup>2</sup>, 1 oz. copper traces, still air.
 FR -4 @ 500 mm<sup>2</sup>, 1 oz. copper traces, still air.

<sup>6.</sup> Pulsed Condition: Pulse Width = 300 msec, Duty Cycle ≤ 2%.

# TYPICAL CHARACTERISTICS MUN2133, MMUN2133L, MUN5133, DTA143ZE, DTA143ZM3

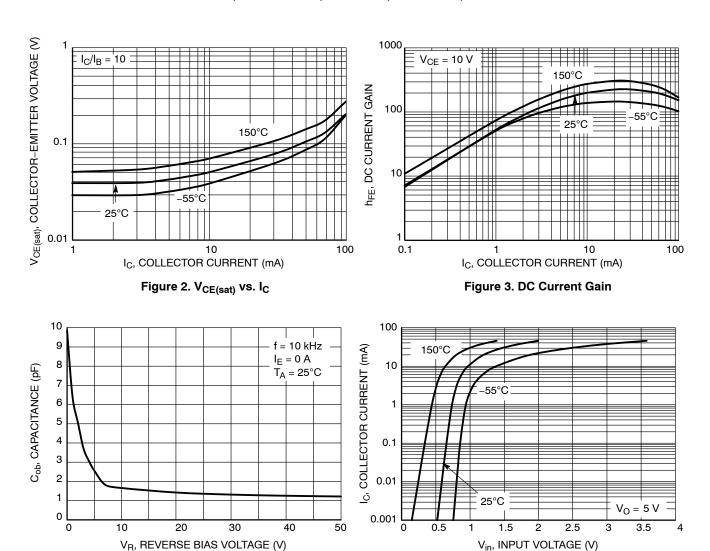


Figure 4. Output Capacitance

Figure 5. Output Current vs. Input Voltage

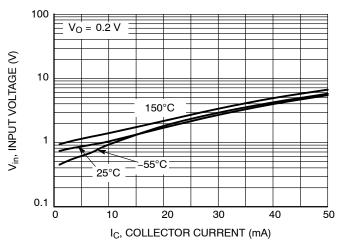


Figure 6. Input Voltage vs. Output Current

### TYPICAL CHARACTERISTICS NSBA143ZF3

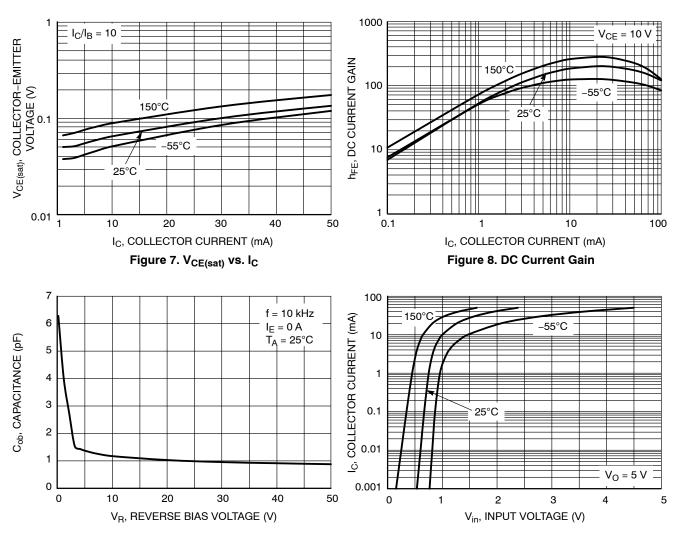


Figure 9. Output Capacitance

Figure 10. Output Current vs. Input Voltage

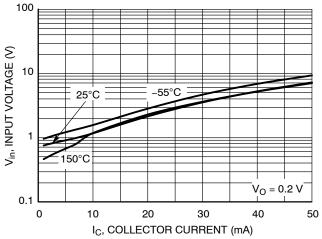


Figure 11. Input Voltage vs. Output Current

#### **PACKAGE DIMENSIONS**



SC-59-3 2.90x1.50x1.15, 1.90P CASE 318D **ISSUE J** 

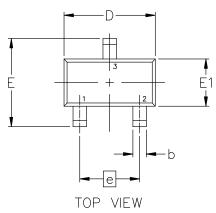
**DATE 15 FEB 2024** 

#### NOTES:

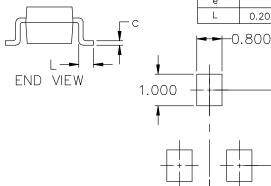
- DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
- ALL DIMENSION ARE IN MILLIMETERS.

	MILLIMETERS			
DIM	MIN.	NOM.	MAX.	
А	1.00	1.15	1.30	
A1	0.01	0.06	0.10	
Ь	0.35	0.43	0.50	
С	0.09	0.14	0.18	
D	2.70	2.90	3.10	
E	2.50	2.80	3.00	
E1	1.30	1.50	1.70	
е	1.90 BSC			
L	0.20	0.40	0.60	

2.400







0.950 -

## RECOMMENDED MOUNTING FOOTPRINT\*

<del>↓</del>0.950

FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.







XXX = Specific Device Code

= Date Code M

= Pb-Free Package\*

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1: PIN 1. BASE STYLE 2: PIN 1. ANODE PIN 1. ANODE 2. EMITTER 2. N.C. 3. CATHODE 3. CATHODE 3. COLLECTOR

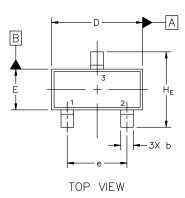
STYLE 4: PIN 1. CATHODE STYLE 5: STYLE 6: PIN 1. CATHODE PIN 1. ANODE 2. CATHODE 2. N.C. 2 CATHODE 3. ANODE 3. ANODE/CATHODE

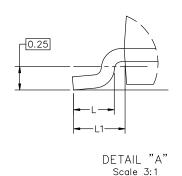


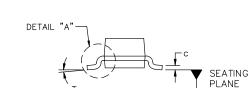


#### SOT-23 (TO-236) 2.90x1.30x1.00 1.90P **CASE 318 ISSUE AU**

**DATE 14 AUG 2024** 







END VIEW



#### NOTES:

- DIMENSIONING AND TOLERANCING 1. PER ASME Y14.5M, 2018. CONTROLLING DIMENSIONS:
- MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE
- BASE MATERIAL.
  DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.



SIDE VIEW

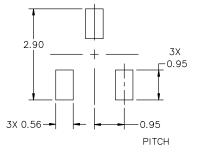


XXX = Specific Device Code

= Date Code

= Pb-Free Package

<sup>\*</sup>This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.



C

#### RECOMMENDED MOUNTING FOOTPRINT

\* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **STYLES ON PAGE 2**

DOCUMENT NUMBER:	98ASB42226B	from the Document Repository. LED COPY" in red.	
DESCRIPTION:	SOT-23 (TO-236) 2.90x1.3	0x1.00 1.90P	PAGE 1 OF 2

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## SOT-23 (TO-236) 2.90x1.30x1.00 1.90P CASE 318 ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	1	
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE		PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE		2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE		3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	N PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Document Reposite Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOT-23 (TO-236) 2.90x1.30x1.00 1.90P		PAGE 2 OF 2	

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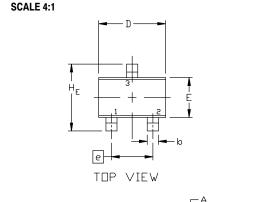
SC-70 (SOT-323) CASE 419 ISSUE R

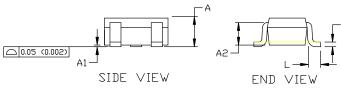
**DATE 11 OCT 2022** 

#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH

	M:	MILLIMETERS			INCHES	
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016
С	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.080	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
е	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC				0.026 BS	C
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095





# GENERIC MARKING DIAGRAM

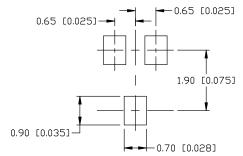


XX = Specific Device Code

M = Date Code

■ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



For additional information on our Pb-Free strategy and soldering details, please download the ID Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

SOLDERING FOOTPRINT

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE	
STYLE 6:	STYLE 7:	STYLE 8:	STYLE 9:	STYLE 10:	STYLE 11:
PIN 1. EMITTER	PIN 1. BASE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. CATHODE
2. BASE	2. EMITTER	2. SOURCE	2. CATHODE	2. ANODE	<ol><li>CATHODE</li></ol>
<ol><li>COLLECTOR</li></ol>	<ol><li>COLLECTOR</li></ol>	3. DRAIN	<ol><li>CATHODE-ANODE</li></ol>	3. ANODE-CATHODE	<ol><li>CATHODE</li></ol>

DOCUMENT NUMBER:	98ASB42819B	ASB42819B Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SC-70 (SOT-323)		PAGE 1 OF 1

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#### SC75-3 1.60x0.80x0.80, 1.00P **CASE 463 ISSUE H**

**DATE 01 FEB 2024** 

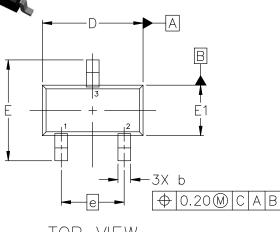
#### NOTES:

- DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
- ALL DIMENSION ARE IN MILLIMETERS.

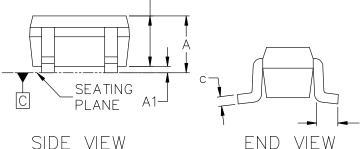
DIM	М	ILLIMETER	RS
	MIN.	NOM.	MAX.
А	0.70	0.80	0.90
A1	0.00	0.05	0.10
A2	0.80 REF.		
Ь	0.15	0.20	0.30
С	0.10	0.15	0.25
D	1.55	1.60	1.65
Е	1.50	1.60	1.70
E1	0.70	0.80	0.90
е		1.00 BSC	,
L	0.10	0.15	0.20

-0.356

0.787



VIEW



Α2

SIDE VIEW

### **GENERIC MARKING DIAGRAM\***



XX= Specific Device Code

Μ = Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1: PIN 1. BASE 2. EMITTER

3. COLLECTOR

STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE

FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

1.000

RECOMMENDED MOUNTING FOOTPRINT\*

1.803

0.508

STYLE 4:	STYLE 5:
PIN 1. CATHODE	PIN 1. GATE
2. CATHODE	2. SOURCE
3 ANODE	3 DRAIN

**DOCUMENT NUMBER:** 

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**DESCRIPTION:** SC75-3 1.60x0.80x0.80, 1.00P

98ASB15184C

**PAGE 1 OF 1** 

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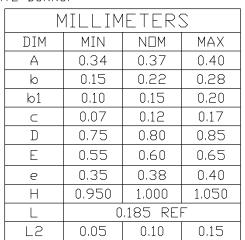


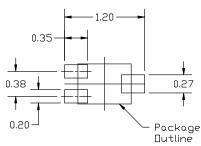
#### SOT-1123 0.80x0.60x0.37, 0.35P CASE 524AA ISSUE D

**DATE 18 JAN 2024** 

#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
  MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS
  OF BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

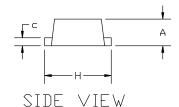




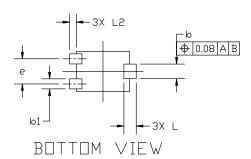
# RECOMMENDED MOUNTING FOOTPRINT

\*For additional information on our Pb-Free strategy and soldering details, please download th e □N Semiconductor Soldering and Mounting Techniques Reference manual, S□LDERRM/D.

<del>-</del> :	D	-A B
		E



THP VIFW



## GENERIC MARKING DIAGRAM\*



X = Specific Device Code

M = Date Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:
PIN 1. BASE
<ol><li>EMITTER</li></ol>
3 COLLECTOR

STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE

STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE

STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE STYLE 5: PIN 1. GATE 2. SOURCE

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DESCRIPTION:	SOT-1123 0.80x0.60x0.37, 0.35P		PAGE 1 OF 1

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MILLIMETERS

 $N\square M$ .

0.50

0.21

0.31

0.12

1.20

0.80

0.40 BSC

1.20



#### SOT-723 1.20x0.80x0.50, 0.40P CASE 631AA ISSUE E

**DATE 24 JAN 2024** 

MAX.

0.55

0.27

0.37

0.17

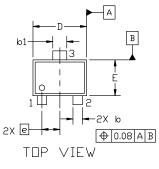
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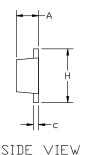
0.85

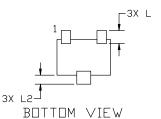
1.25

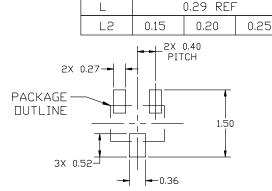
#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
- 3, MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH, MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.









DIM

Α

b

b1

c D

Ε

e H MIN.

0.45

0.15

0.25

0.07

1.15

0.75

1.15

## RECOMMENDED MOUNTING FOOTPRINT

\*For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

## GENERIC MARKING DIAGRAM\*



XX = Specific Device Code M = Date Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1: STYLE 2: STYLE 3: STYLE 4: STYLE 5: PIN 1. GATE 2. SOURCE PIN 1. BASE PIN 1. ANODE PIN 1. ANODE PIN 1. CATHODE 2 FMITTER N/C
 CATHODE 2. ANODE3. CATHODE 2 CATHODE COLLECTOR 3. ANODE 3. DRAIN

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DESCRIPTION:	SOT-723 1.20x0.80x0.50, 0.40P		PAGE 1 OF 1

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